



**THE DATASHEET OF
IGW75N60T**

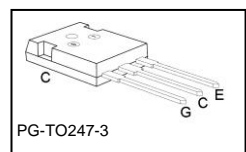
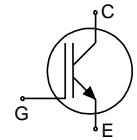


Low Loss IGBT: IGBT in TRENCHSTOP™ and Fieldstop technology



Features:

- Very low $V_{CE(sat)}$ 1.5V (typ.)
- Maximum Junction Temperature 175°C
- Short circuit withstand time 5 μ s
- Designed for :
 - Frequency Converters
 - Uninterrupted Power Supply
- TRENCHSTOP™ and Fieldstop technology for 600V applications offers :
 - very tight parameter distribution
 - high ruggedness, temperature stable behavior
 - very high switching speed
- Positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Qualified according to JEDEC¹ for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	V_{CE}	I_C	$V_{CE(sat), T_j=25^\circ C}$	$T_{j,max}$	Marking	Package
IGW75N60T	600V	75A	1.5V	175°C	G75T60	PG-TO247-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j \geq 25^\circ C$	V_{CE}	600	V
DC collector current, limited by $T_{j,max}$	I_C	118	A
$T_C = 25^\circ C$		85	
$T_C = 100^\circ C$		225	
Pulsed collector current, t_p limited by $T_{j,max}$		$I_{C,puls}$	
Turn off safe operating area $V_{CE} = 600V, T_j = 175^\circ C, t_p = 1\mu s$	-	225	
Gate-emitter voltage	V_{GE}	± 20	V
Short circuit withstand time ²⁾	t_{SC}	5	μs
$V_{GE} = 15V, V_{CC} \leq 400V, T_j \leq 150^\circ C$			
Power dissipation $T_C = 25^\circ C$	P_{tot}	428	W
Operating junction temperature	T_j	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

¹ J-STD-020 and JESD-022

²⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		0.35	K/W
Thermal resistance, junction – ambient	R_{thJA}		40	

Electrical Characteristic, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=0.2mA$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=75A$ $T_j=25\text{ °C}$ $T_j=175\text{ °C}$	-	1.5	2.0	
			-	1.9	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=1.2mA, V_{CE}=V_{GE}$	4.1	4.9	5.7	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600V, V_{GE}=0V$ $T_j=25\text{ °C}$ $T_j=175\text{ °C}$	-	-	40	μA
			-	-	5000	
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE}=20V, I_C=75A$	-	41	-	S
Integrated gate resistor	R_{Gint}			-		Ω

Dynamic Characteristic

Input capacitance	C_{iss}	$V_{CE}=25V, V_{GE}=0V, f=1MHz$	-	4620	-	μF
Output capacitance	C_{oss}		-	288	-	
Reverse transfer capacitance	C_{rss}		-	137	-	
Gate charge	Q_{Gate}	$V_{CC}=480V, I_C=75A, V_{GE}=15V$	-	470	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13	-	nH
Short circuit collector current ¹⁾	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 5\mu s, V_{CC} = 400V, T_j \leq 150\text{ °C}$	-	687.5	-	A

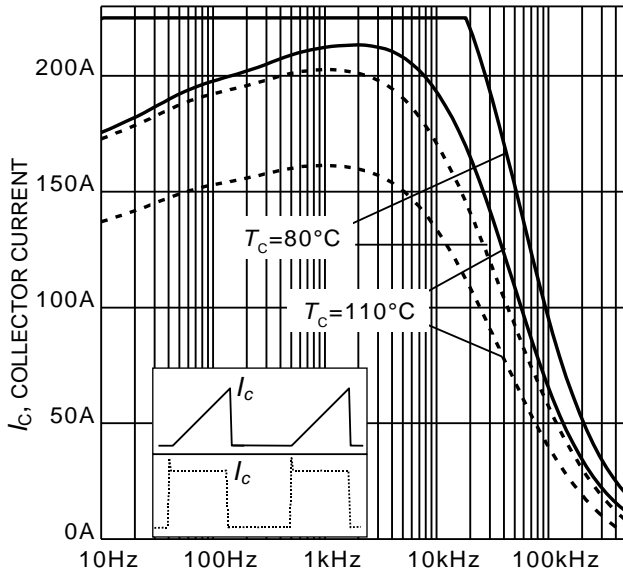
¹⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.

Switching Characteristic, Inductive Load, at $T_j=25\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=25\text{ °C}$, $V_{CC}=400\text{V}$, $I_C=75\text{A}$, $V_{GE}=0/15\text{V}$, $r_G=5\Omega$, $L_\sigma=100\text{nH}$, $C_\sigma=39\text{pF}$	-	33	-	ns
Rise time	t_r		-	36	-	
Turn-off delay time	$t_{d(off)}$		-	330	-	
Fall time	t_f		-	35	-	
Turn-on energy ¹⁾	E_{on}	L_σ , C_σ from Fig. E Energy losses include "tail" and diode reverse recovery. Diode from IKW75N60T	-	2.0	-	mJ
Turn-off energy	E_{off}		-	2.5	-	
Total switching energy	E_{ts}		-	4.5	-	

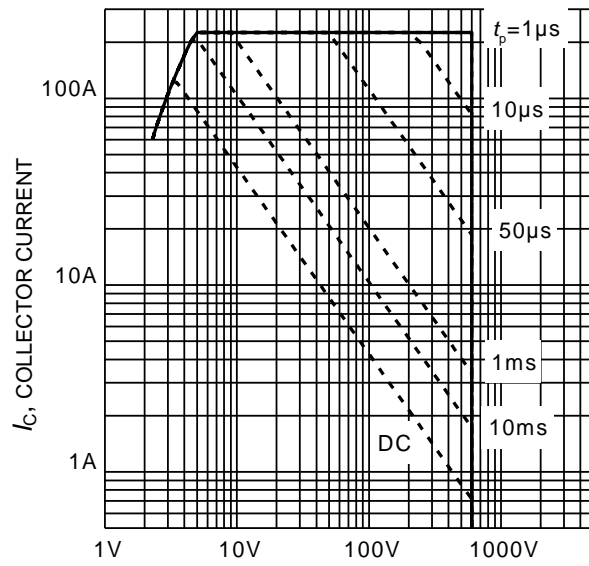
Switching Characteristic, Inductive Load, at $T_j=175\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=175\text{ °C}$, $V_{CC}=400\text{V}$, $I_C=75\text{A}$, $V_{GE}=0/15\text{V}$, $r_G=5\Omega$, $L_\sigma=100\text{nH}$, $C_\sigma=39\text{pF}$	-	32	-	ns
Rise time	t_r		-	37	-	
Turn-off delay time	$t_{d(off)}$		-	363	-	
Fall time	t_f		-	38	-	
Turn-on energy ¹⁾	E_{on}	L_σ , C_σ from Fig. E Energy losses include "tail" and diode reverse recovery. Diode from IKW75N60T	-	2.9	-	mJ
Turn-off energy	E_{off}		-	2.9	-	
Total switching energy	E_{ts}		-	5.8	-	



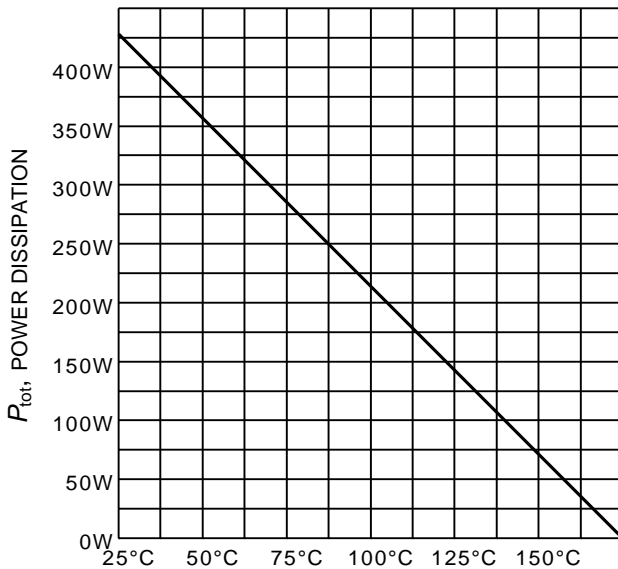
f , SWITCHING FREQUENCY

Figure 1. Collector current as a function of switching frequency
 ($T_j \leq 175^\circ\text{C}$, $D = 0.5$, $V_{CE} = 400\text{V}$,
 $V_{GE} = 0/15\text{V}$, $r_G = 5\Omega$)



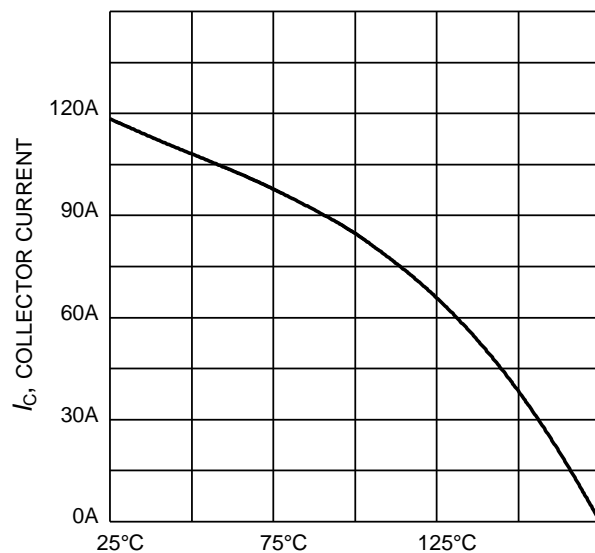
V_{CE} , COLLECTOR-EMITTER VOLTAGE

Figure 2. Safe operating area
 ($D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 175^\circ\text{C}$;
 $V_{GE} = 0/15\text{V}$)



T_C , CASE TEMPERATURE

Figure 3. Power dissipation as a function of case temperature
 ($T_j \leq 175^\circ\text{C}$)



T_C , CASE TEMPERATURE

Figure 4. DC Collector current as a function of case temperature
 ($V_{GE} \geq 15\text{V}$, $T_j \leq 175^\circ\text{C}$)

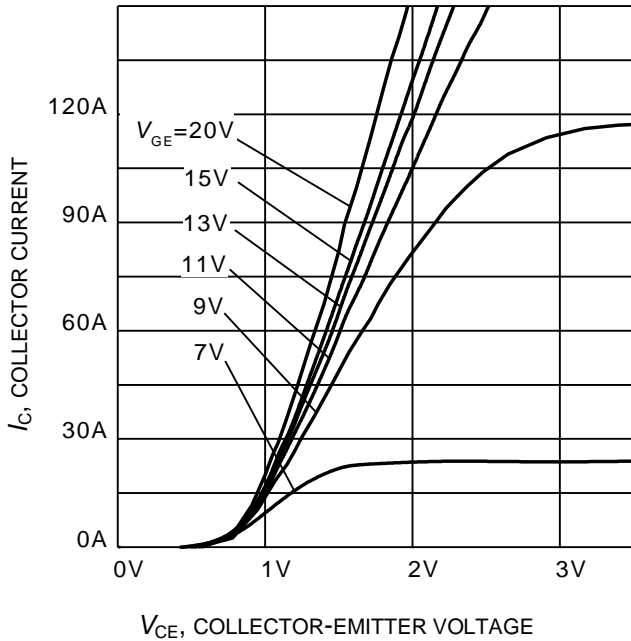


Figure 5. Typical output characteristic
($T_j = 25^\circ\text{C}$)

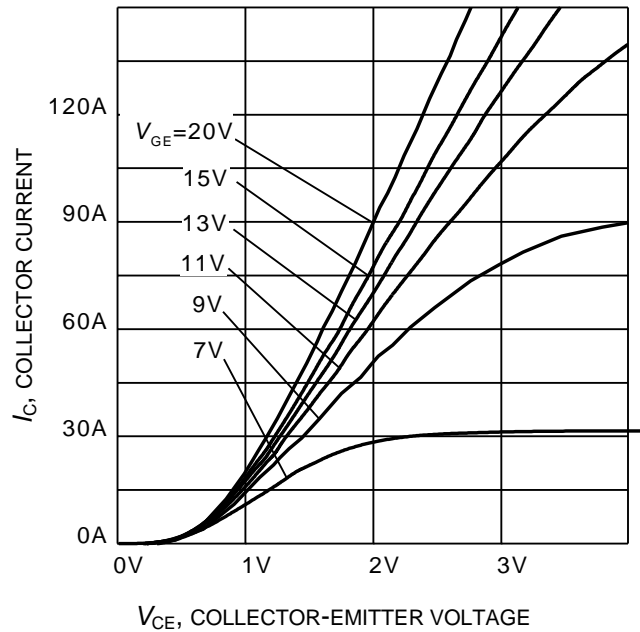


Figure 6. Typical output characteristic
($T_j = 175^\circ\text{C}$)

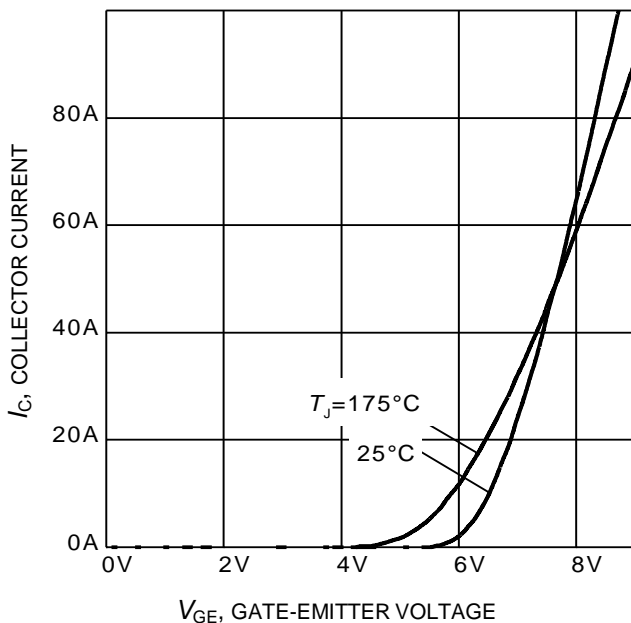


Figure 7. Typical transfer characteristic
($V_{CE} = 20\text{V}$)

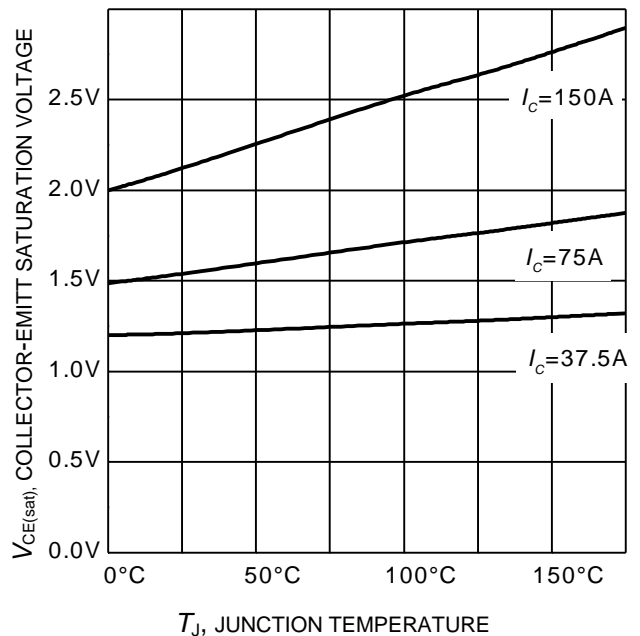


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 15\text{V}$)

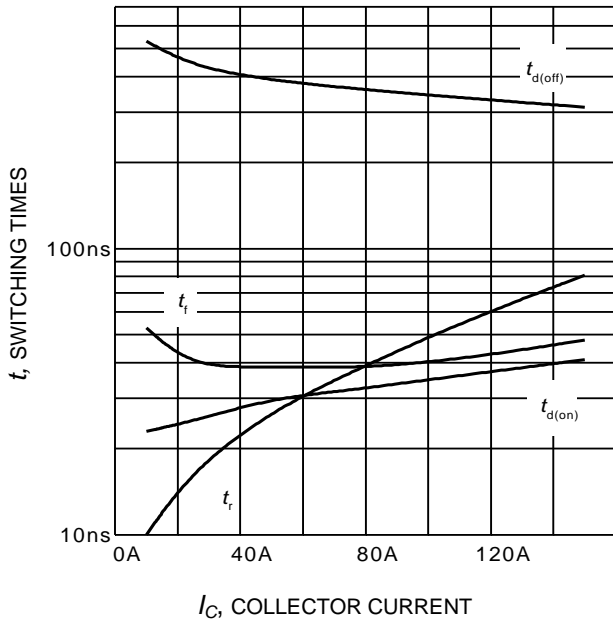


Figure 9. Typical switching times as a function of collector current
 (inductive load, $T_J=175^\circ\text{C}$,
 $V_{CE} = 400\text{V}$, $V_{GE} = 0/15\text{V}$, $r_G = 5\Omega$,
 Dynamic test circuit in Figure E)

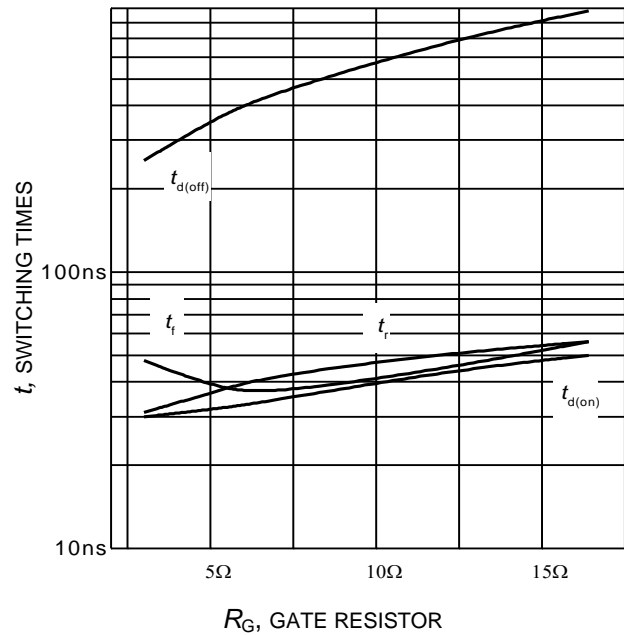


Figure 10. Typical switching times as a function of gate resistor
 (inductive load, $T_J = 175^\circ\text{C}$,
 $V_{CE} = 400\text{V}$, $V_{GE} = 0/15\text{V}$, $I_C = 75\text{A}$,
 Dynamic test circuit in Figure E)

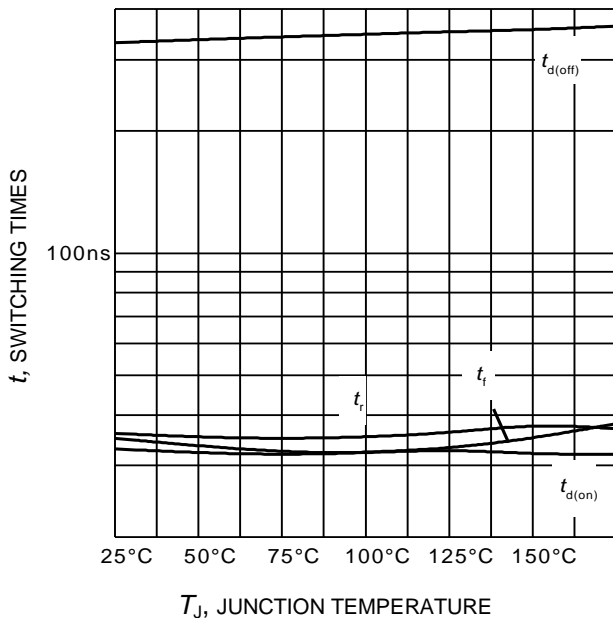


Figure 11. Typical switching times as a function of junction temperature
 (inductive load, $V_{CE} = 400\text{V}$,
 $V_{GE} = 0/15\text{V}$, $I_C = 75\text{A}$, $r_G = 5\Omega$,
 Dynamic test circuit in Figure E)

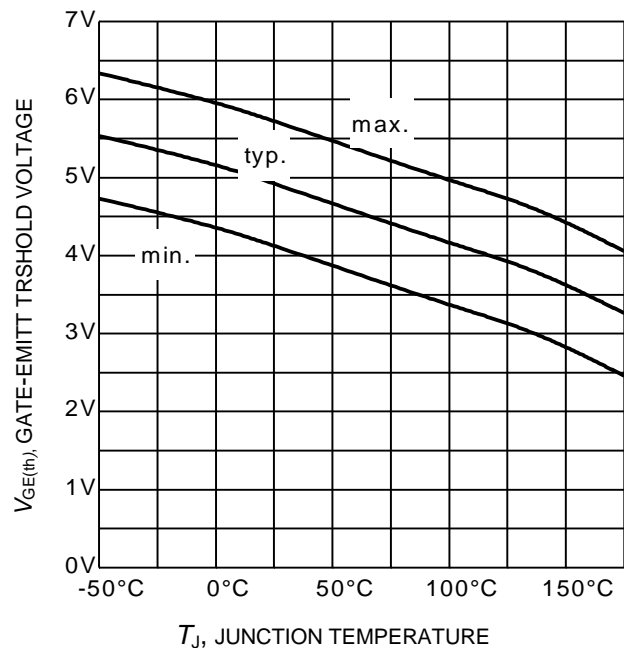


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
 ($I_C = 1.2\text{mA}$)

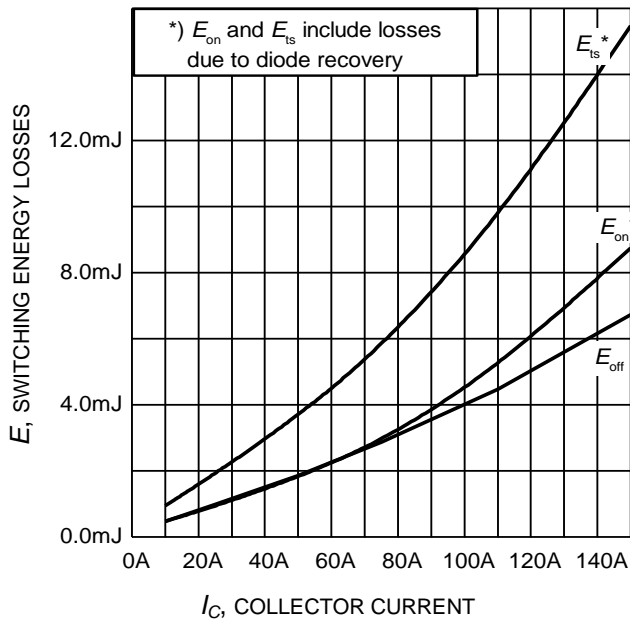


Figure 13. Typical switching energy losses as a function of collector current
 (inductive load, $T_J = 175^\circ\text{C}$,
 $V_{CE} = 400\text{V}$, $V_{GE} = 0/15\text{V}$, $r_G = 5\Omega$,
 Dynamic test circuit in Figure E)

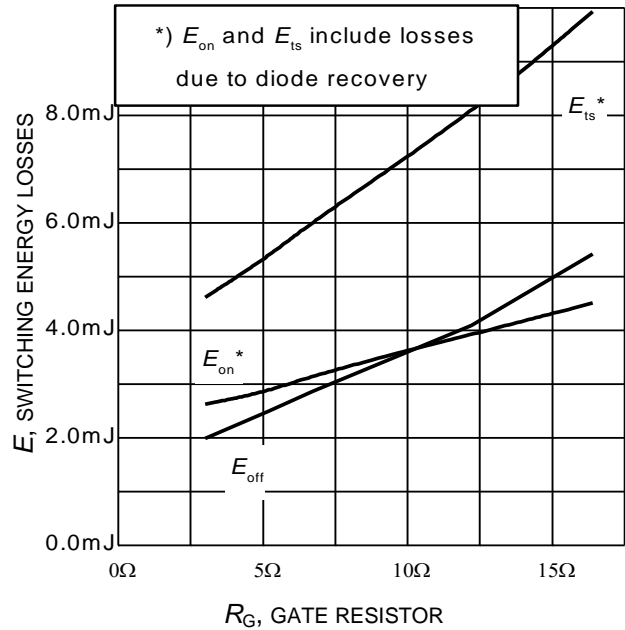


Figure 14. Typical switching energy losses as a function of gate resistor
 (inductive load, $T_J = 175^\circ\text{C}$,
 $V_{CE} = 400\text{V}$, $V_{GE} = 0/15\text{V}$, $I_C = 75\text{A}$,
 Dynamic test circuit in Figure E)

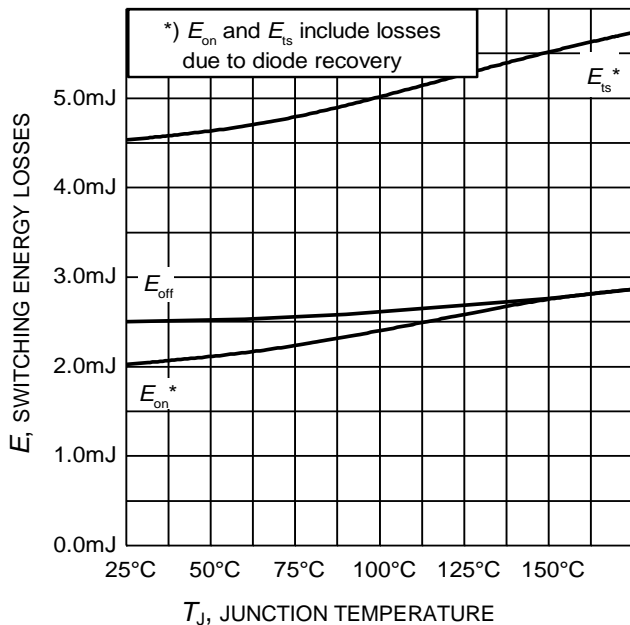


Figure 15. Typical switching energy losses as a function of junction temperature
 (inductive load, $V_{CE} = 400\text{V}$,
 $V_{GE} = 0/15\text{V}$, $I_C = 75\text{A}$, $r_G = 5\Omega$,
 Dynamic test circuit in Figure E)

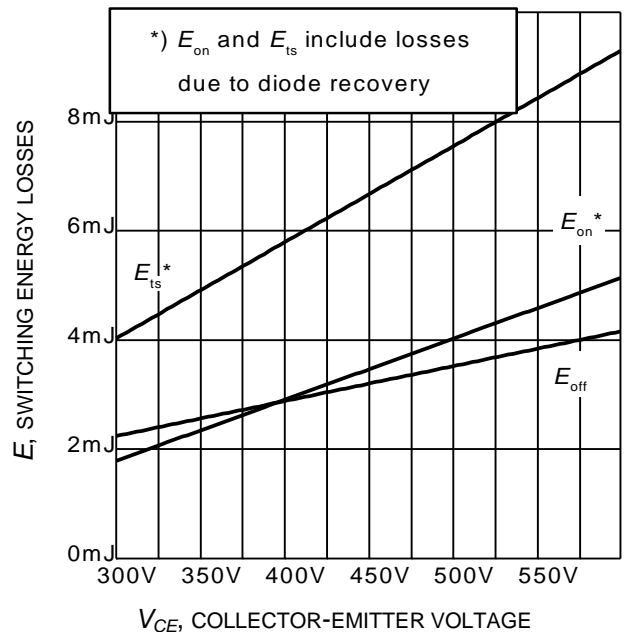


Figure 16. Typical switching energy losses as a function of collector emitter voltage
 (inductive load, $T_J = 175^\circ\text{C}$,
 $V_{GE} = 0/15\text{V}$, $I_C = 75\text{A}$, $r_G = 5\Omega$,
 Dynamic test circuit in Figure E)

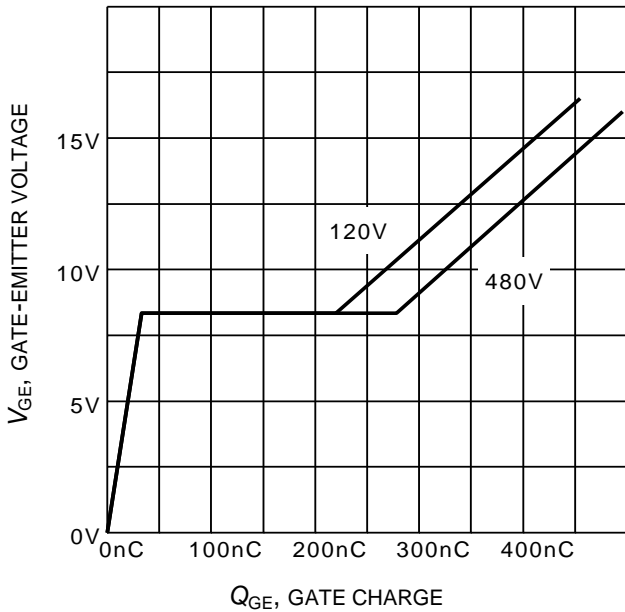


Figure 17. Typical gate charge
($I_C=75\text{ A}$)

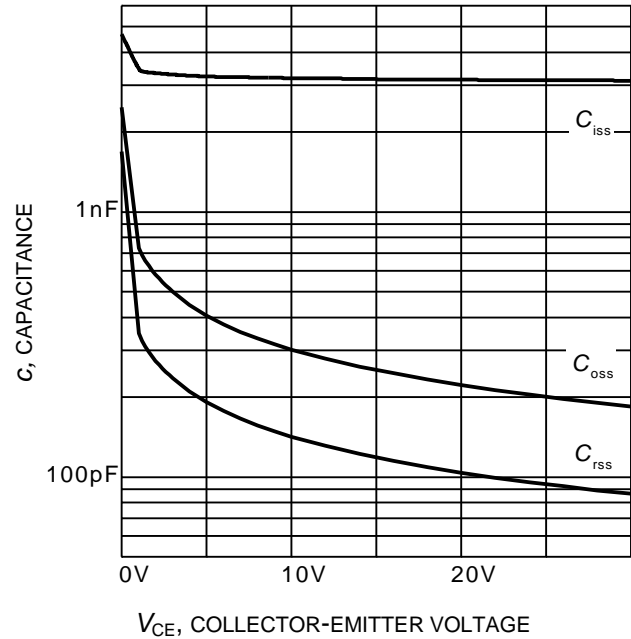


Figure 18. Typical capacitance as a function of collector-emitter voltage
($V_{GE}=0\text{V}$, $f = 1\text{ MHz}$)

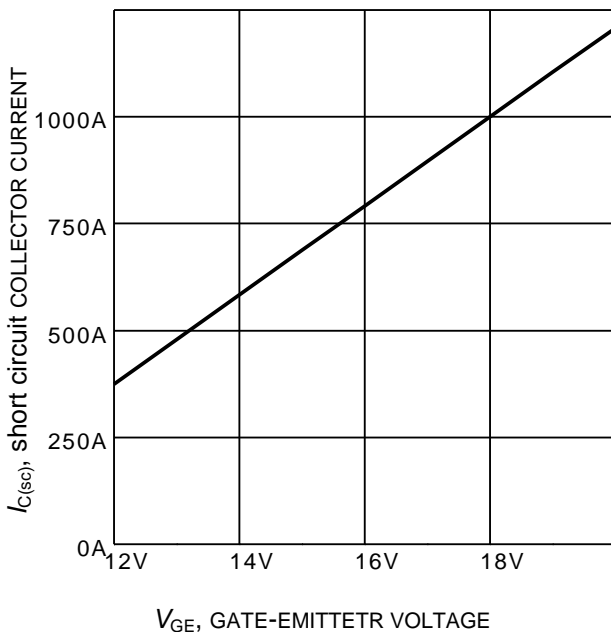


Figure 19. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq 400\text{V}$, $T_j \leq 150^\circ\text{C}$)

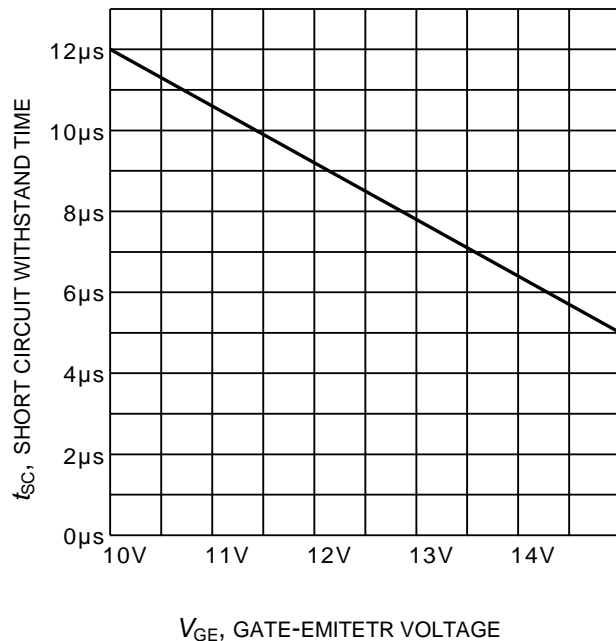


Figure 20. Short circuit withstand time as a function of gate-emitter voltage
($V_{CE}=400\text{V}$, start at $T_j=25^\circ\text{C}$, $T_{jmax}<150^\circ\text{C}$)

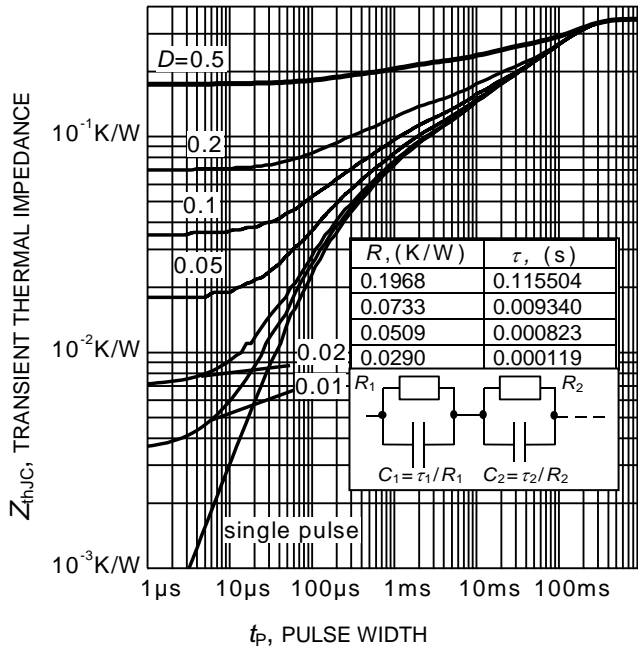
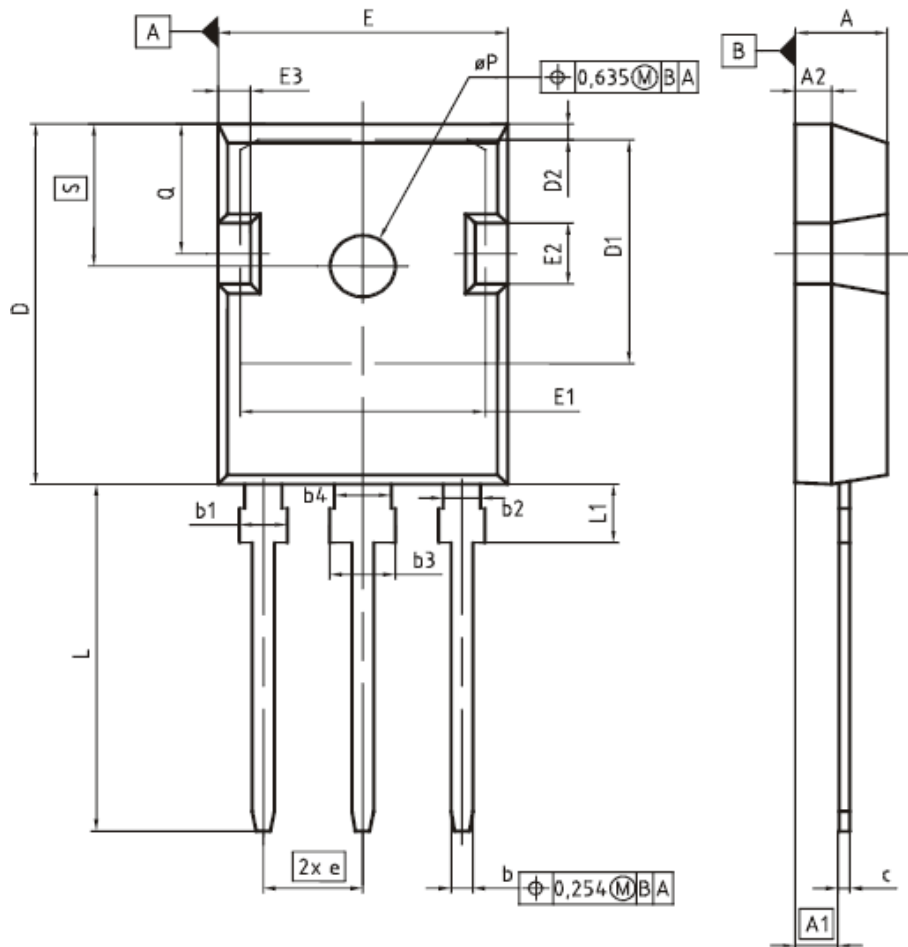


Figure 21. IGBT transient thermal impedance
 $(D = t_p / T)$

PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4,83	5,21	0,190	0,205
A1	2,27	2,54	0,089	0,100
A2	1,85	2,16	0,073	0,085
b	1,07	1,33	0,042	0,052
b1	1,90	2,41	0,075	0,095
b2	1,90	2,16	0,075	0,085
b3	2,87	3,38	0,113	0,133
b4	2,87	3,13	0,113	0,123
c	0,55	0,68	0,022	0,027
D	20,80	21,10	0,819	0,831
D1	16,25	17,65	0,640	0,695
D2	0,95	1,35	0,037	0,053
E	15,70	16,13	0,618	0,635
E1	13,10	14,15	0,516	0,557
E2	3,68	5,10	0,145	0,201
E3	1,00	2,60	0,039	0,102
e	5,44 (BSC)		0,214 (BSC)	
N	3		3	
L	19,80	20,32	0,780	0,800
L1	4,10	4,47	0,161	0,176
sP	3,50	3,70	0,138	0,146
Q	5,49	6,00	0,216	0,236
S	6,04	6,30	0,238	0,248

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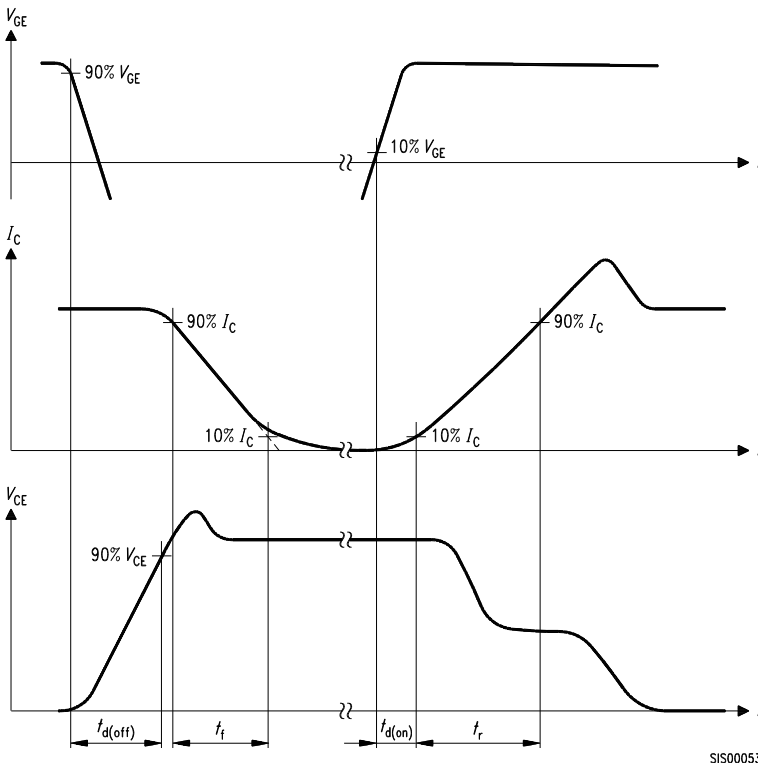


Figure A. Definition of switching times

SIS00053

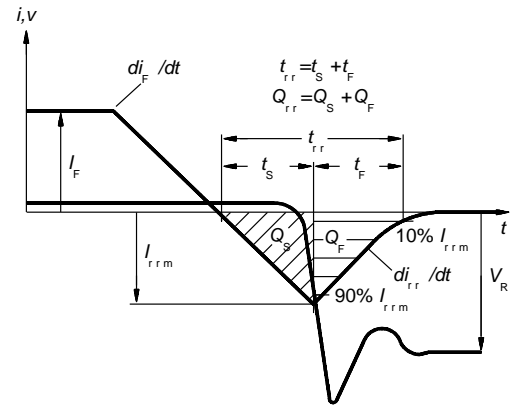


Figure C. Definition of diodes switching characteristics

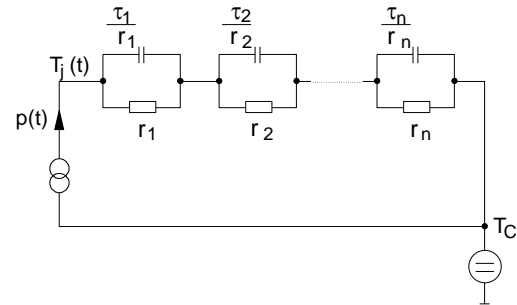


Figure D. Thermal equivalent circuit

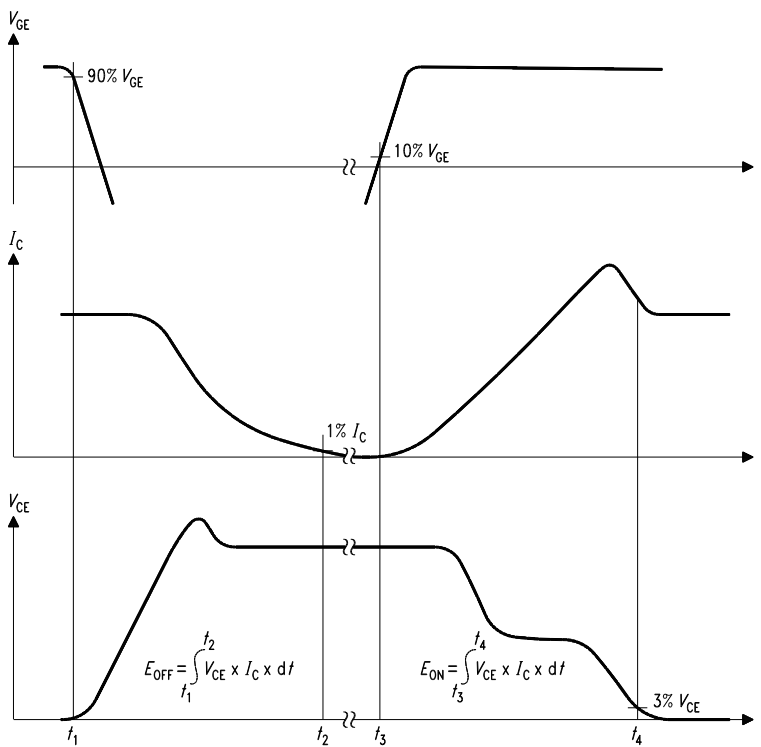


Figure B. Definition of switching losses

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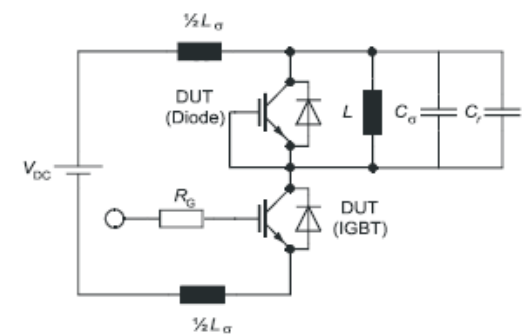


Figure E. Dynamic test circuit
Parasitic inductance L_{σ} ,
Parasitic capacitor C_{σ} ,
Relief capacitor C_r ,
(only for ZVT switching)

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